

1-Line Bidirectional ESD Protection Diode



General description

Low capacitance bidirectional ElectroStatic Discharge (ESD) protection diode in a DFN1006(SOD882) leadless ultra small Surface-Mounted Device (SMD) plastic package designed to protect one signal line from the damage caused by ESD and other transients.

Features and benefits

- Bidirectional ESD protection of one line
- Femtofarad capacitance: $C_j = 10\text{pF}$ (Typ)
- Response time is typically $< 1\text{ ns}$
- Low clamping voltage $V_C = 40\text{ V}$
- Ultra Low Leakage: nA Level
- IEC 61000-4-2; level 4 (ESD)
- IEC 61000-4-5 (surge); $I_{PPM} = 4\text{ A}$

Application information

- Portable electronics
- Computers and peripherals
- Audio and video equipment
- Cellular handsets and accessories
- Communication systems
- Power supplies

Ordering information

Device	Package	Marking	Packaging
SLESD8D24CS	DFN1006-2L	CG4	10000/Tape & Reel

Schematic & Pin configuration

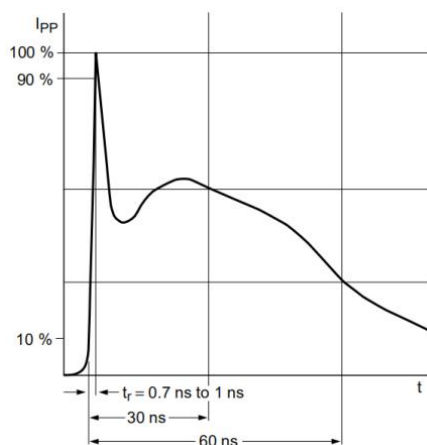
Simplified outline	Graphic symbol

Maximum Ratings ($T_{OP} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

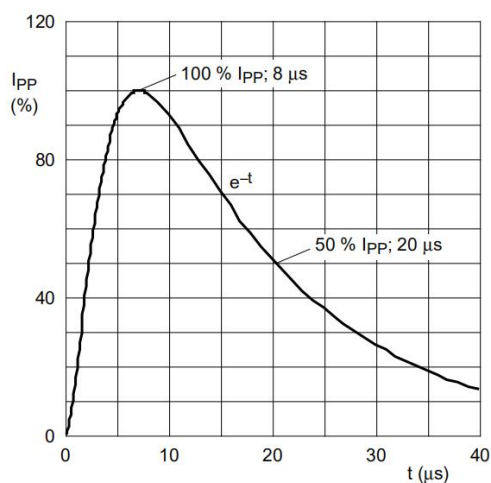
Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_p = 8/20\text{ }\mu\text{s}$)	P_{PPM}	160	W
Rated Peak Pulse Current ($T_p = 8/20\text{ }\mu\text{s}$)	I_{PPM}	4	A
Maximum lead temperature for soldering during 10s	T_L	260	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$
Operating Temperature Range	T_{OP}	-40 to +125	$^{\circ}\text{C}$
Maximum junction temperature	T_j	150	$^{\circ}\text{C}$
ESD voltage IEC 61000-4-2 (air discharge)	V_{ESD}	20	kV
ESD voltage IEC 61000-4-2 (contact discharge)	V_{ESD}	15	kV

Electrical Characteristics ($T_{OP} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Reverse Working Voltage	V_{RWM}	--	--	24.0	V	
Breakdown Voltage	V_{BR}	26.0	--	30.0	V	$I_T=1\text{mA}$
Leakage Current I_{Leak}	I_R	--	--	100	nA	$V_{RWM}=24\text{V}$
Clamping Voltage	V_C	--	28	30.0	V	$I_{PP}=1.0\text{A}, T_p=8/20\mu\text{s}$
Clamping Voltage	V_C	--	39	40.0	V	$I_{PP}=4.0\text{A}, T_p=8/20\mu\text{s}$
Junction Capacitance	C_j	--	10	12	pF	$V_R=0\text{V}, f=1\text{MHz}$



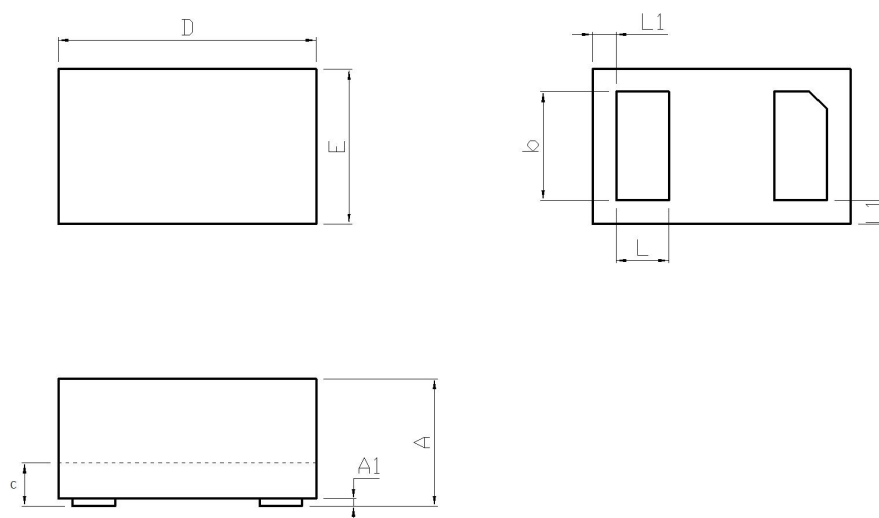
IEC61000-4-2 Waveform



IEC 61000-4-5 Waveform(8/20μs pulse)

Package Outline Dimensions

DFN1006-2L



DFN1006-2L (mm)			
Dim	Min	Typ.	Max
A	0.46	0.48	0.50
A1	0	0.02	0.05
b	0.45	0.5	0.55
c	0.1	0.12	0.14
D	0.95	1.00	1.05
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.035	0.05	0.065
h	0.07	0.12	0.17